

Jiahuan

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Planar Direction-Dependent Interfacial Properties in Monolayer In ₂ Se ₃ "Metal Contacts. Physica Status Solidi (B): Basic Research, 2020, 257, 1900198.	1.5	19
2	Sub-5-nm Monolayer Silicane Transistor: A First-Principles Quantum Transport Simulation. Physical Review Applied, 2020, 14, .	3.8	38
3	First-principles simulation of monolayer hydrogen passivated Bi ₂ O ₂ S ₂ "metal interfaces. Physical Chemistry Chemical Physics, 2020, 22, 7853-7863.	2.8	9
4	Reexamination of the Schottky Barrier Heights in Monolayer MoS ₂ Field-Effect Transistors. ACS Applied Nano Materials, 2019, 2, 4717-4726.	5.0	27
5	Computational Study of Ohmic Contact at Bilayer InSe-Metal Interfaces: Implications for Field-Effect Transistors. ACS Applied Nano Materials, 2019, 2, 6898-6908.	5.0	13
6	Bilayer tellurene "metal interfaces. Journal of Semiconductors, 2019, 40, 062003.	3.7	9
7	Interfacial Properties of Monolayer Antimonene Devices. Physical Review Applied, 2019, 11, .	3.8	22
8	Excellent Device Performance of Sub-5-nm Monolayer Tellurene Transistors. Advanced Electronic Materials, 2019, 5, 1900226.	5.1	65
9	Monolayer GaS with high ion mobility and capacity as a promising anode battery material. Journal of Materials Chemistry A, 2019, 7, 14042-14050.	10.3	32
10	Pervasive Ohmic Contacts in Bilayer Bi ₂ O ₂ Se "Metal Interfaces. Journal of Physical Chemistry C, 2019, 123, 8923-8931.	3.1	17
11	Unusual Fermi-Level Pinning and Ohmic Contact at Monolayer Bi ₂ O ₂ Se "Metal Interface. Advanced Theory and Simulations, 2019, 2, 1800178.	2.8	20
12	Schottky Contact in Monolayer WS ₂ Field-Effect Transistors. Advanced Theory and Simulations, 2019, 2, 1900001.	2.8	42
13	Sub 10 nm Bilayer Bi ₂ O ₂ Se Transistors. Advanced Electronic Materials, 2019, 5, 1800720.	5.1	70
14	Gate-tunable interfacial properties of in-plane ML MX ₂ 1T "2H heterojunctions. Journal of Materials Chemistry C, 2018, 6, 5651-5661.	5.5	54
15	n-Type Ohmic contact and p-type Schottky contact of monolayer InSe transistors. Physical Chemistry Chemical Physics, 2018, 20, 24641-24651.	2.8	33
16	n- and p-type ohmic contacts at monolayer gallium nitride "metal interfaces. Physical Chemistry Chemical Physics, 2018, 20, 24239-24249.	2.8	13
17	Monolayer tellurene "metal contacts. Journal of Materials Chemistry C, 2018, 6, 6153-6163.	5.5	81